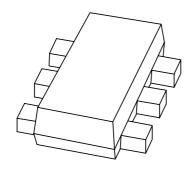
DISCRETE SEMICONDUCTORS

DATA SHEET



PEMH7

NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = open

Preliminary specification

2001 Oct 22





NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = open

PEMH7

FEATURES

- 300 mW total power dissipation
- Very small 1.6 × 1.2 mm ultra thin package
- Self alignment during soldering due to straight leads
- Replaces two SC-75/SC-89 packaged transistors on same PCB area
- Reduces required PCB area
- Reduced pick and place costs.

APPLICATIONS

- · General purpose switching and amplification
- · Inverter and interface circuits
- · Circuit driver.

DESCRIPTION

NPN resistor-equipped transistors in a SOT666 plastic package.

MARKING

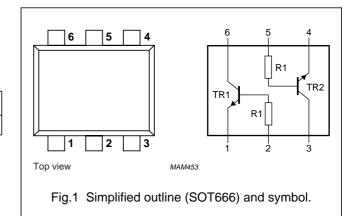
TYPE NUMBER	MARKING CODE
PEMH7	H3

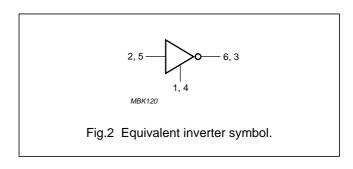
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V _{CEO}	collector-emitter voltage	50	V
I _{CM}	peak collector current	100	mA
TR1	NPN	_	_
TR2	NPN	_	_
R1	bias resistor	4.7	kΩ
R2	open	_	_

PINNING

PIN	DESCRIPTION		
1, 4	emitter	TR1; TR2	
2, 5	base	TR1; TR2	
6, 3	collector	TR1; TR2	





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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	PARAMETER CONDITIONS		MAX.	UNIT
Per transis	Per transistor				
V _{CBO}	collector-base voltage	open emitter	-	50	V
V _{CEO}	collector-emitter voltage	open base	-	50	V
V _{EBO}	emitter-base voltage	open collector	-	5	V
Io	output current (DC)		_	100	mA
I _{CM}	peak collector current		-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	-	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C
Per device	Per device				
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	300	mW

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	notes 1 and 2	416	K/W

Notes

- 1. Transistor mounted on an FR4 printed-circuit board.
- 2. The only recommended soldering method is reflow soldering.

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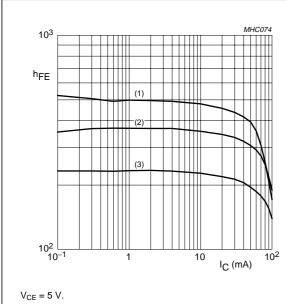
NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = open

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CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER CONDITIONS		MIN.	TYP.	MAX.	UNIT
Per transis	stor					
I _{CBO}	collector-base cut-off current	V _{CB} = 50 V; I _E = 0	_	_	100	nA
I _{CEO}	collector-emitter cut-off current	V _{CE} = 50 V; I _B = 0	_	_	1	μΑ
		$V_{CE} = 30 \text{ V}; I_{B} = 0; T_{j} = 150 ^{\circ}\text{C}$	_	_	50	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0	_	_	100	nA
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 1 mA	200	330	_	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 5 \text{ mA}; I_B = 0.25 \text{ mA}$	_	_	100	mV
R1	input resistor		3.3	4.7	6.1	kΩ
C _c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = 10 \text{ V}$; $f = 1 \text{ MHz}$	_	_	2.5	pF



- (1) $T_{amb} = 100 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -40 \, ^{\circ}C$.

Fig.3 DC current gain as a function of collector current; typical values.

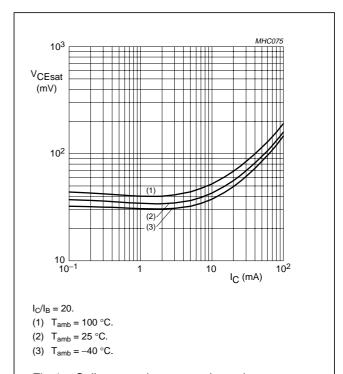


Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.

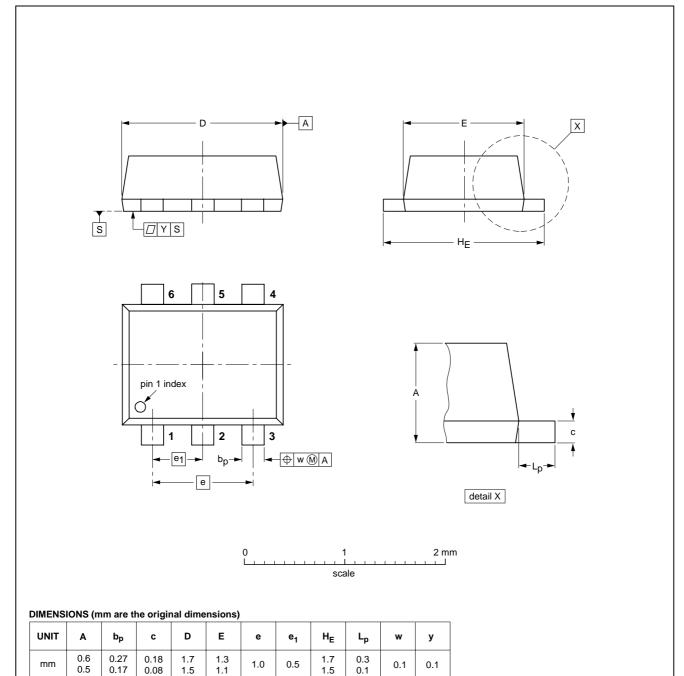
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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT666



OUTLINE	REFERENCES		EUROPEAN	ICCUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION ISSUE DAT	
SOT666						-01-01-04 01-08-27

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DATA SHEET STATUS(1)	PRODUCT STATUS ⁽²⁾	DEFINITIONS
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Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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